



MMBD914

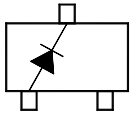
Silicon Epitaxial Planar Switching Diode

Features

- Low forward voltage
- Fast reverse recovery time

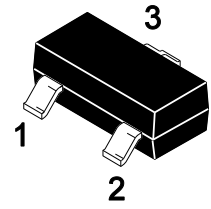
Equivalent Circuit

3.Cathode



1.Anode 2.NC

SOT-23



Marking Code : 5D

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current ($t = 1 \mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$)

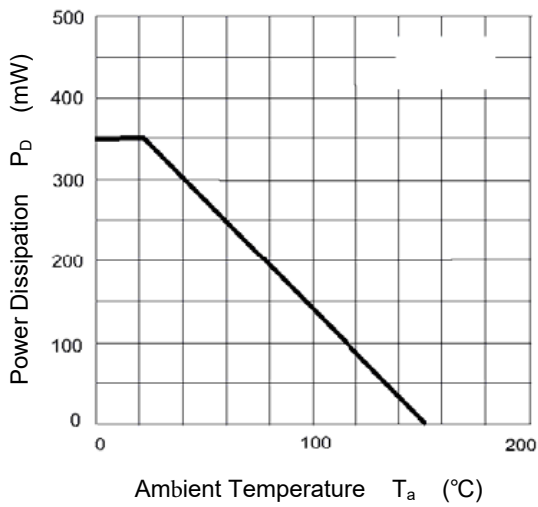
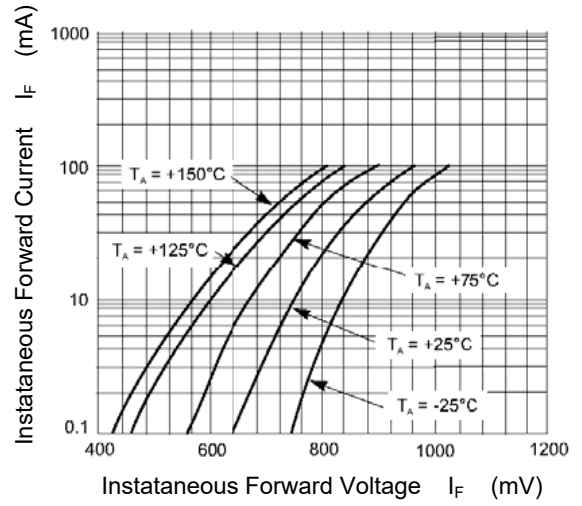
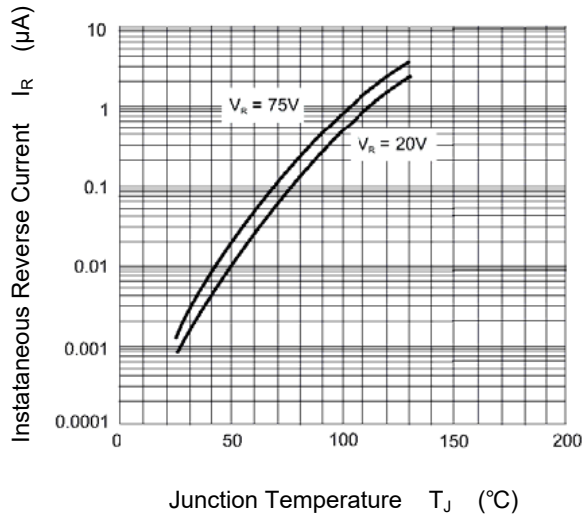
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10 \text{ mA}$	V_F	--	1	V
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	100	--	V
Reverse Current at $V_R = 20 \text{ V}$	I_R	--	25	nA
at $V_R = 75 \text{ V}$		--	5	μA
Typical Junction Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_j	--	4	pF
Maximum Reverse Recovery Time at $I_F = I_R = 10 \text{ mA}$	T_{rr}	--	4	nS



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Typical Characteristic Curves





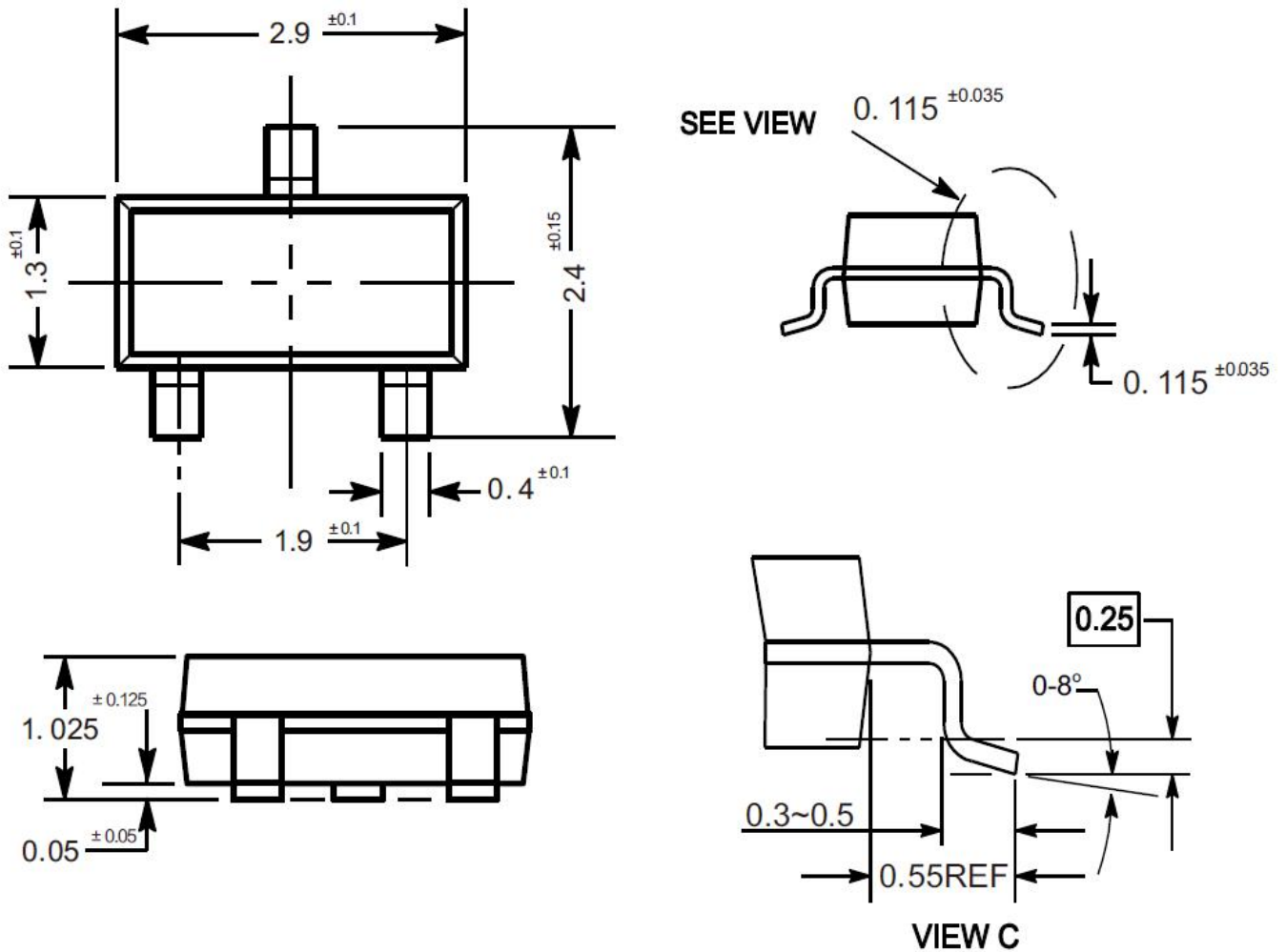
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Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
MMBD914	SOT-23	3,000PCS/Reel&7inches